P10A/REV01

TRANSMITTAL OF INFORMATION DISCLO (Under 37 CFR 1.97(b) or 1.97		Docket No
In Re Application Of: Shire SARAI et al.		C 1700
Serial No. 10/044,686 Filing Date January 11, 2002	Examiner	Group Art Unit 1765
Title: NITRIDE SEMICONDUCTOR CHIP AND METI SEMICONDUCTOR CHIP	HOD FOR MANUFACTURIN	1.17(p))
Paym (Only complete if Applicant elects	ent of Fee to pay the fee set forth in 37 CFR	1.17(p))
□ A check in the amount of is atta The Assistant Commissioner is hereby authorized as described below. A duplicate copy of this shee □ Charge the amount of □ Credit any overpayment. □ Charge any additional fee required. Certificate of Transmission by Facsimile* I certify that this document and authorization to charge deposit account is being facsimile transmitted to the United States Patent and Trademark Office (Fax. No.) on (Date) Signature *This certificate may only be used if paying by deposit account.	Certificate of Maili Certify that this docume on 5-10-02. first class mail under 37 C.F. Assistant Commissioner for 20231. Signature of Person Tawana	ing by First Class Mail ent and fee is being deposited with the U.S. Postal Service as F.R. 1.8 and is addressed to the or Patents, Washington, D.C. Mailing Correspondence a L. Garcia Person Mailing Correspondence
Jonathan P. Osha, Reg. No. 33,986 ROSENTHAL & OSHA L.L.P. 1221 McKinney Avenue, Suite 2800 Houston, Texas 77010	Dated.	
Telephone: 713-228-8600 Facsimile: 713-228-8778	,	
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